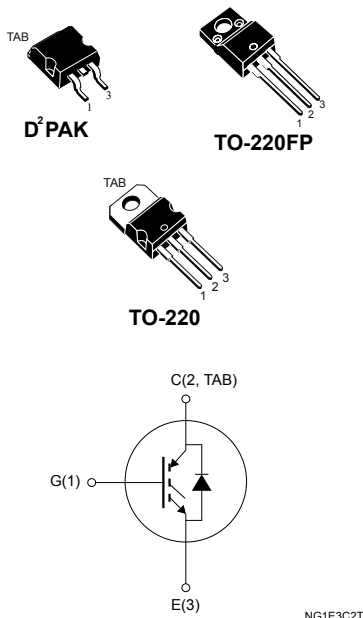




Trench gate field-stop 600 V, 20 A high speed IGBT



Features

- Maximum junction temperature: $T_J = 175\text{ }^{\circ}\text{C}$
- High speed switching
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance
- Short-circuit rated
- Soft and fast recovery antiparallel diode

Applications

- Industrial motor control
- PFC converters, single phase input
- Uninterruptable power supplies (UPS)

Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. These devices are part of the H series of IGBTs, which represents an optimum compromise between conduction and switching losses to maximize the efficiency of high switching frequency converters. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.



Product status links

[STGB20H60DF](#)

[STGF20H60DF](#)

[STGP20H60DF](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK, TO-220	TO-220FP	
V _{CES}	Collector-emitter voltage (V _{GE} = 0 V)	600		V
I _C	Continuous collector current at T _C = 25 °C	40	40 ⁽¹⁾	A
	Continuous collector current at T _C = 100 °C	20	20 ⁽¹⁾	
I _{CP} ⁽²⁾	Pulsed collector current	80	80	A
V _{GE}	Gate-emitter voltage	±20		V
I _F	Diode RMS forward current at T _C = 25 °C	40	40 ⁽¹⁾	A
	Diode RMS forward current at T _C = 100 °C	20	20 ⁽¹⁾	
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T _C = 25 °C)	-	2.5	kV
I _{FP} ⁽²⁾	Pulsed forward current	80	80	A
P _{TOT}	Total power dissipation at T _C = 25 °C	167	37	W
T _{STG}	Storage temperature range	-55 to 150		°C
T _J	Operating junction temperature range	-55 to 175		°C

1. Limited by maximum junction temperature.

2. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		D ² PAK, TO-220	TO-220FP	
R _{thJC}	Thermal resistance, junction-to-case IGBT	0.9	4	°C/W
	Thermal resistance, junction-to-case diode	2.5	5.6	
R _{thJA}	Thermal resistance, junction-to-ambient	62.5		°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 2\text{ mA}$	600	-	-	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$	-	1.6	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$, $T_J = 125\text{ °C}$	-	1.75	-	
		$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$, $T_J = 175\text{ °C}$	-	1.8	-	
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5.0	6.0	7.0	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$	-	-	25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$	-	-	± 250	nA

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	2750	-	pF
C_{oes}	Output capacitance		-	110	-	pF
C_{res}	Reverse transfer capacitance		-	65	-	pF
Q_g	Total gate charge	$V_{CC} = 390\text{ V}$, $I_C = 20\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see the Figure 26. Gate charge test circuit)	-	115	-	nC
Q_{ge}	Gate-emitter charge		-	22	-	nC
Q_{gc}	Gate-collector charge		-	45	-	nC

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see the Figure 24. Test circuit for inductive load switching and Figure 27. Switching waveform)	-	42.5	-	ns
t_r	Current rise time		-	11.9	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1345	-	A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see the the Figure 24. Test circuit for inductive load switching and Figure 27. Switching waveform)	-	42.5	-	ns
t_r	Current rise time		-	13.4	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1180	-	A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see the the Figure 24. Test circuit for inductive load switching and Figure 27. Switching waveform)	-	20	-	ns
$t_{d(off)}$	Turn-off delay time		-	177	-	ns
t_f	Current fall time		-	55	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see the the Figure 24. Test circuit for inductive load switching and Figure 27. Switching waveform)	-	26	-	ns
$t_{d(off)}$	Turn-off delay time		-	173	-	ns
t_f	Current fall time		-	86	-	ns
t_{sc}	Short-circuit withstand time	$V_{CC} \leq 360\text{ V}$, $V_{GE} = 15\text{ V}$, $R_G = 47\ \Omega$	3	5	-	μ s

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see the Figure 27. Switching waveform)	-	209	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	261	-	μ J
E_{ts}	Total switching energy		-	470	-	μ J
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 400\text{ V}$, $I_C = 20\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see the Figure 27. Switching waveform)	-	480	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	416	-	μ J
E_{ts}	Total switching energy		-	896	-	μ J

1. Including the reverse recovery of the diode.
2. Including the tail of the collector current.

Table 7. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 20\text{ A}$	-	1.8	2.2	V
		$I_F = 20\text{ A}, T_J = 175\text{ °C}$	-	1.3	-	
t_{rr}	Reverse recovery time	$I_F = 20\text{ A}, V_R = 60\text{ V}, di/dt = 100\text{ A}/\mu\text{s}$	-	90	-	ns
Q_{rr}	Reverse recovery charge	(see the Figure 25. Diode reverse recovery waveform)	-	110	-	nC
I_{rrm}	Reverse recovery current		-	2.4	-	A
t_{rr}	Reverse recovery time	$I_F = 20\text{ A}, V_R = 60\text{ V}, di/dt = 100\text{ A}/\mu\text{s},$	-	180	-	ns
Q_{rr}	Reverse recovery charge	$T_J = 175\text{ °C}$	-	466	-	nC
I_{rr}	Reverse recovery current	(see the Figure 25. Diode reverse recovery waveform)	-	5.2	-	A

2.1 Electrical characteristics (curves)

Figure 1. Total power dissipation vs temperature D²PAK and TO-220

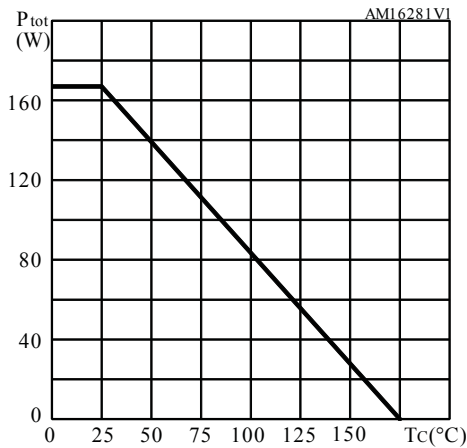


Figure 2. Collector current vs case temperature for TO-220FP

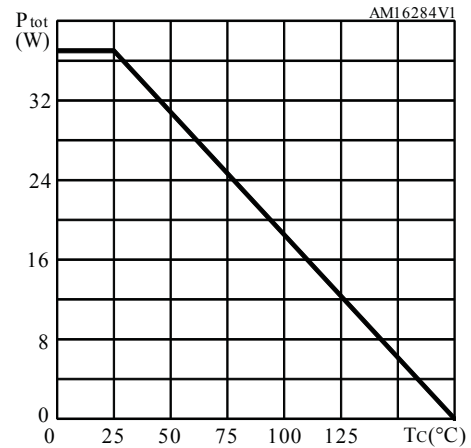


Figure 3. Collector current vs case temperature for D²PAK and TO-220

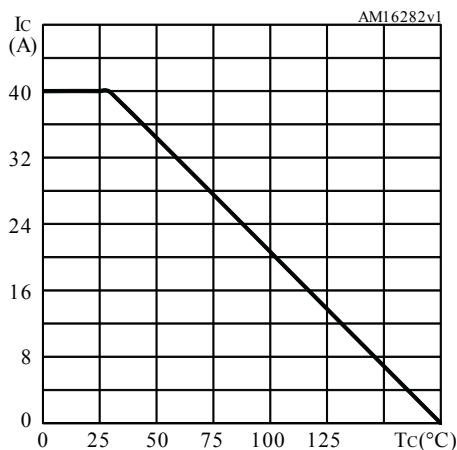


Figure 4. Collector current vs case temperature for TO-220FP

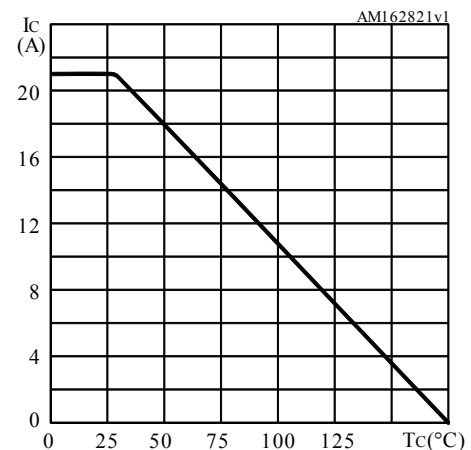


Figure 5. Collector current vs switching frequency for D²PAK and TO-220

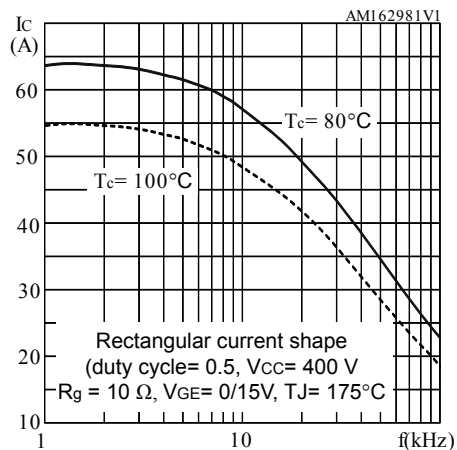


Figure 6. Collector current vs switching frequency for TO-220FP

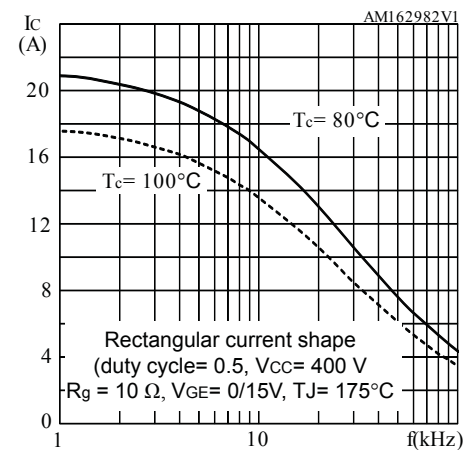


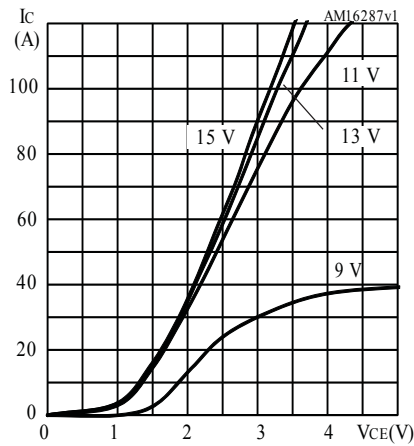
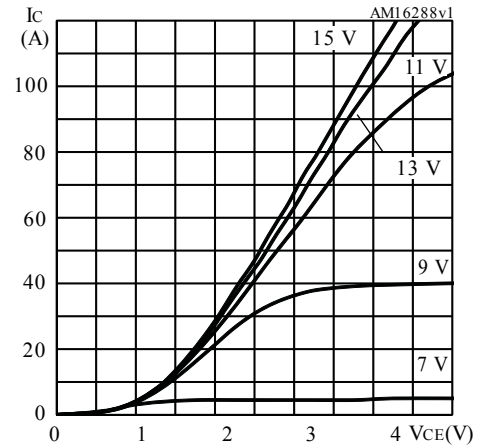
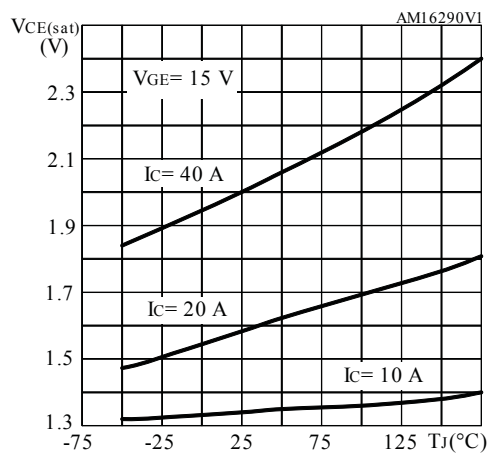
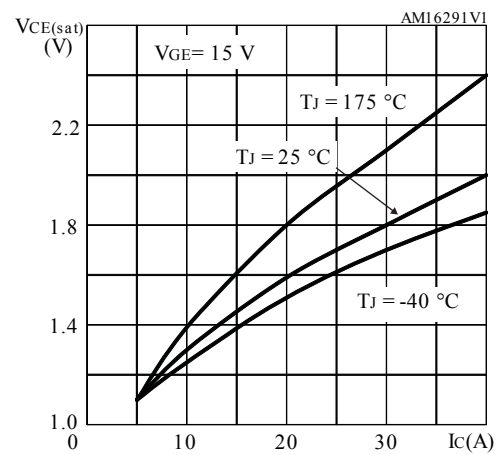
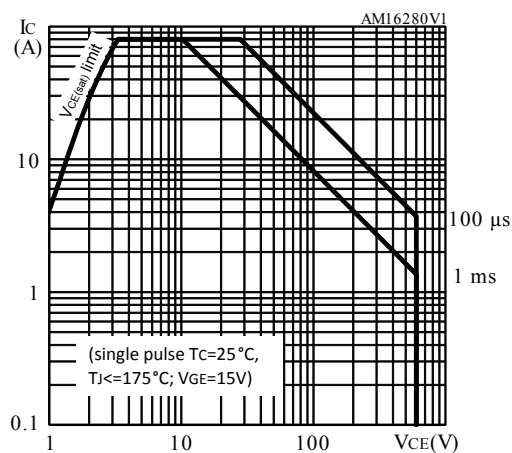
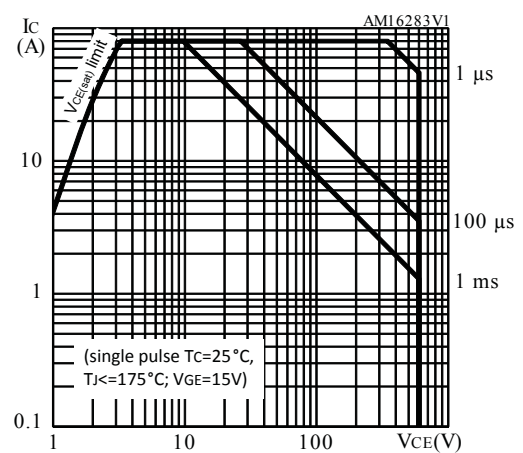
Figure 7. Output characteristics ($T_J = 25^\circ\text{C}$)

Figure 8. Output characteristics ($T_J = 175^\circ\text{C}$)

Figure 9. $V_{CE(sat)}$ vs junction temperature

Figure 10. $V_{CE(sat)}$ vs collector current

Figure 11. Safe operating area for D²PAK and TO-220

Figure 12. Safe operating area for TO-220FP


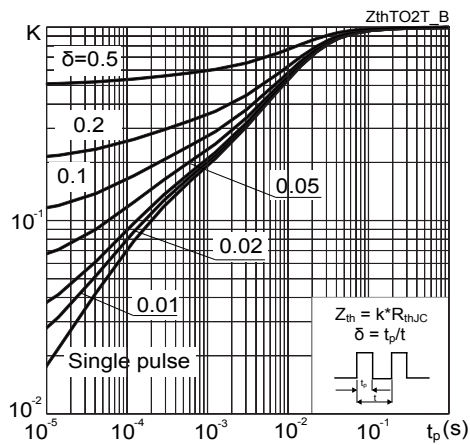
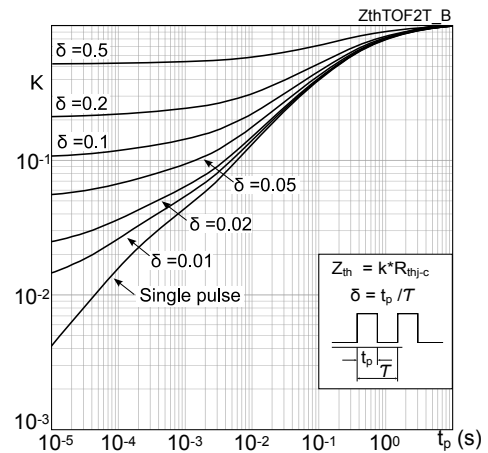
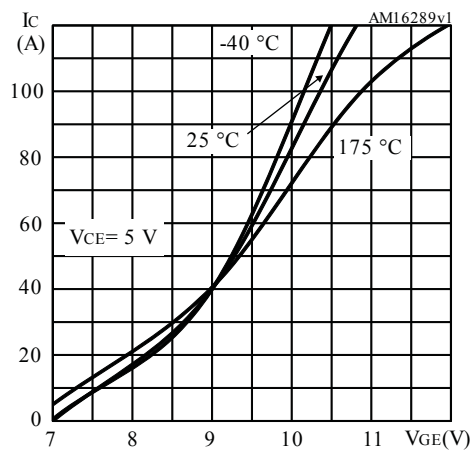
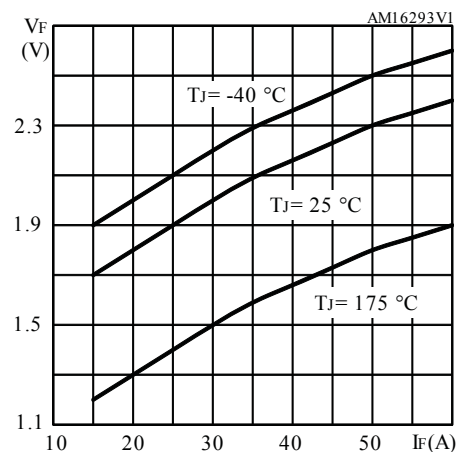
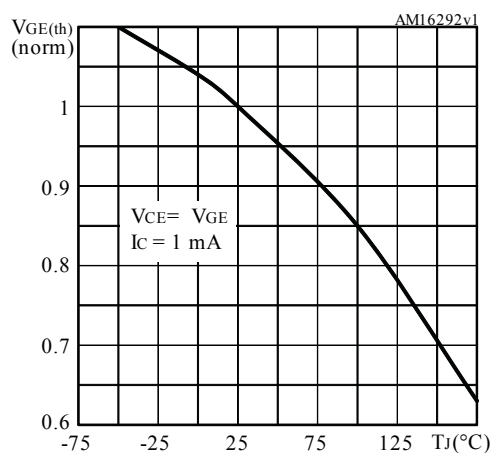
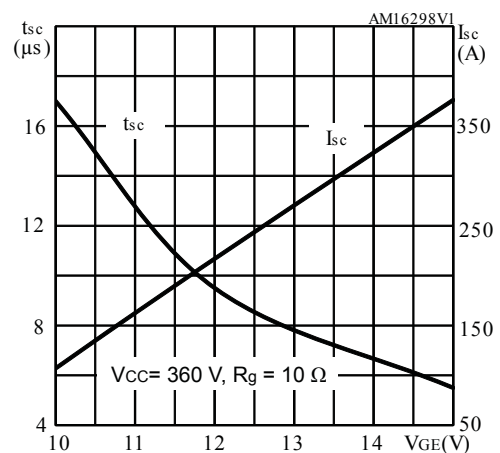
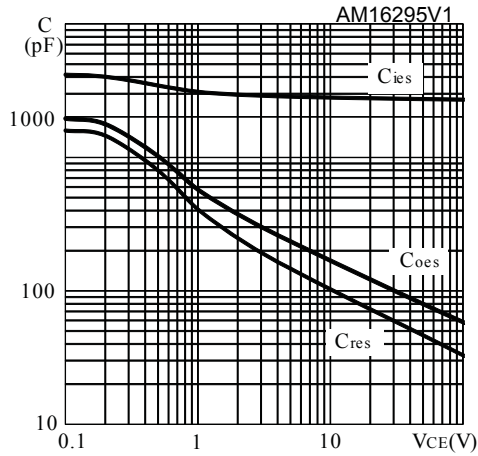
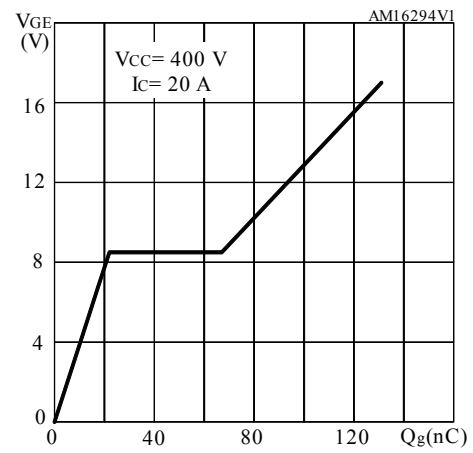
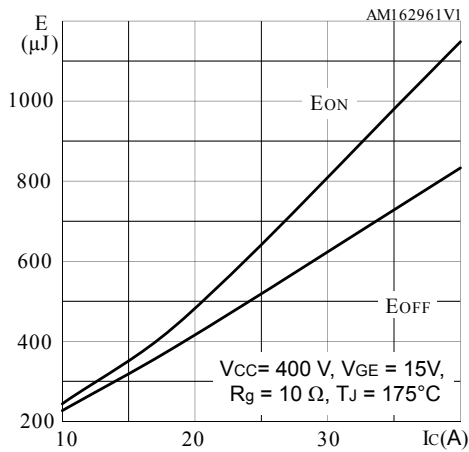
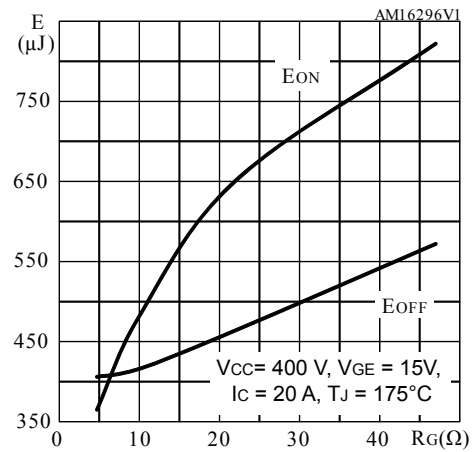
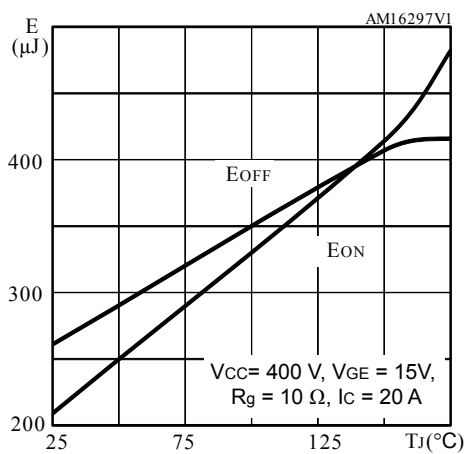
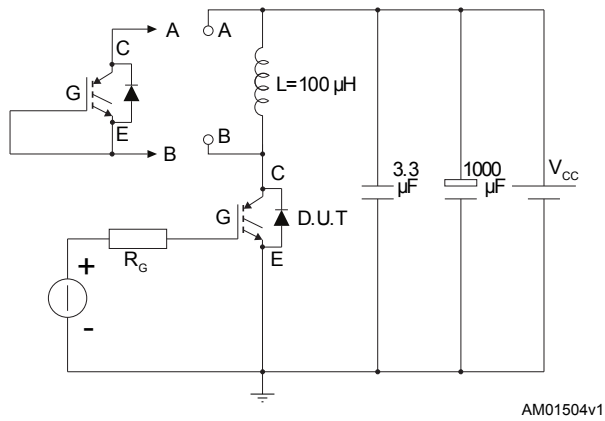
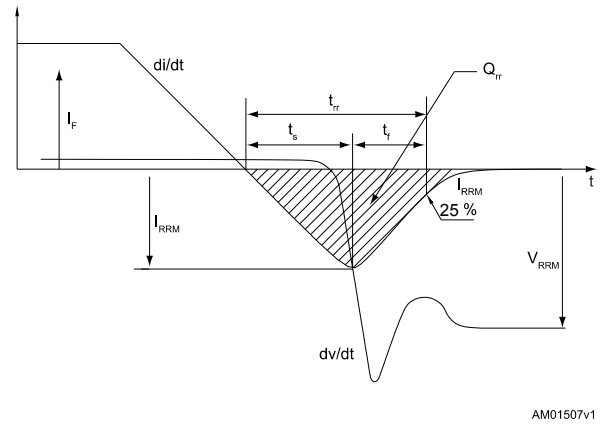
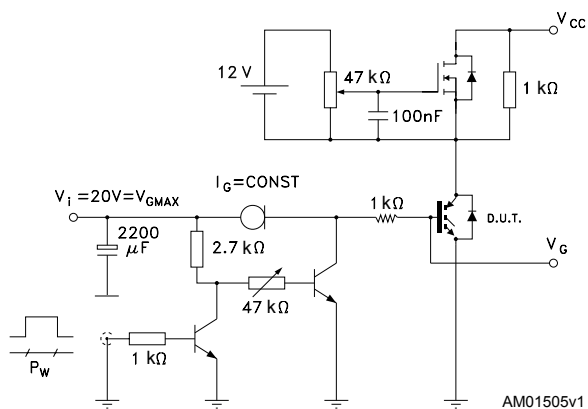
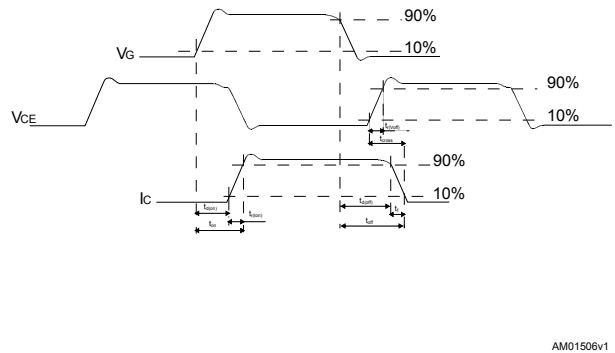
Figure 13. Thermal impedance for D2PAK and TO-220

Figure 14. Thermal impedance for TO-220FP

Figure 15. Transfer characteristics

Figure 16. Diode VF vs forward current

Figure 17. Normalized VGE(th) vs junction temperature

Figure 18. Short-circuit time and current vs VGE


Figure 19. Capacitance variations

Figure 20. Gate charge vs gate-emitter voltage

Figure 21. Switching energy vs collector current

Figure 22. Switching energy vs gate resistance

Figure 23. Switching energy vs temperature


3 Test circuits

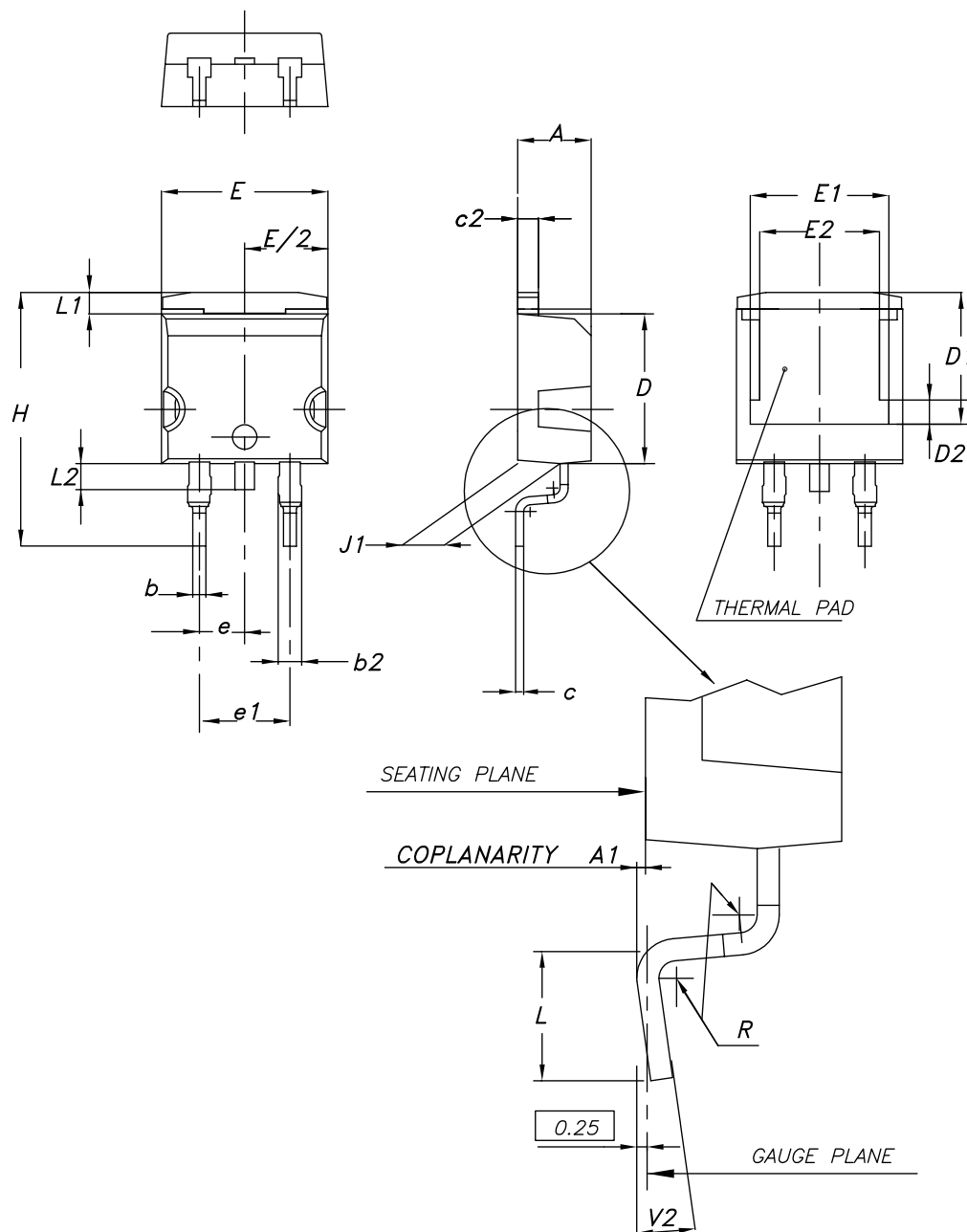
Figure 24. Test circuit for inductive load switching

Figure 25. Diode reverse recovery waveform

Figure 26. Gate charge test circuit

Figure 27. Switching waveform


4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A2 package information

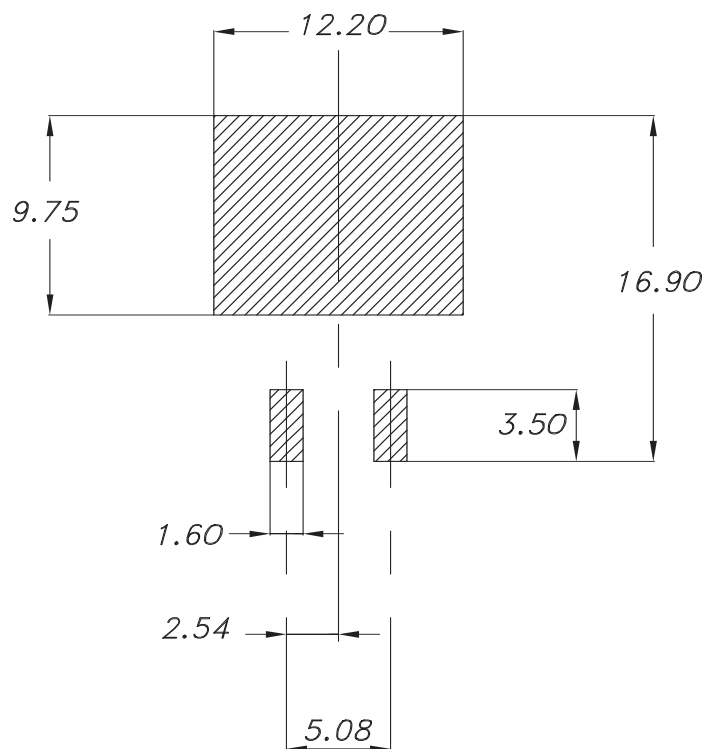
Figure 28. D²PAK (TO-263) type A2 package outline



0079457_A2_27

Table 8. D²PAK (TO-263) type A2 package mechanical data

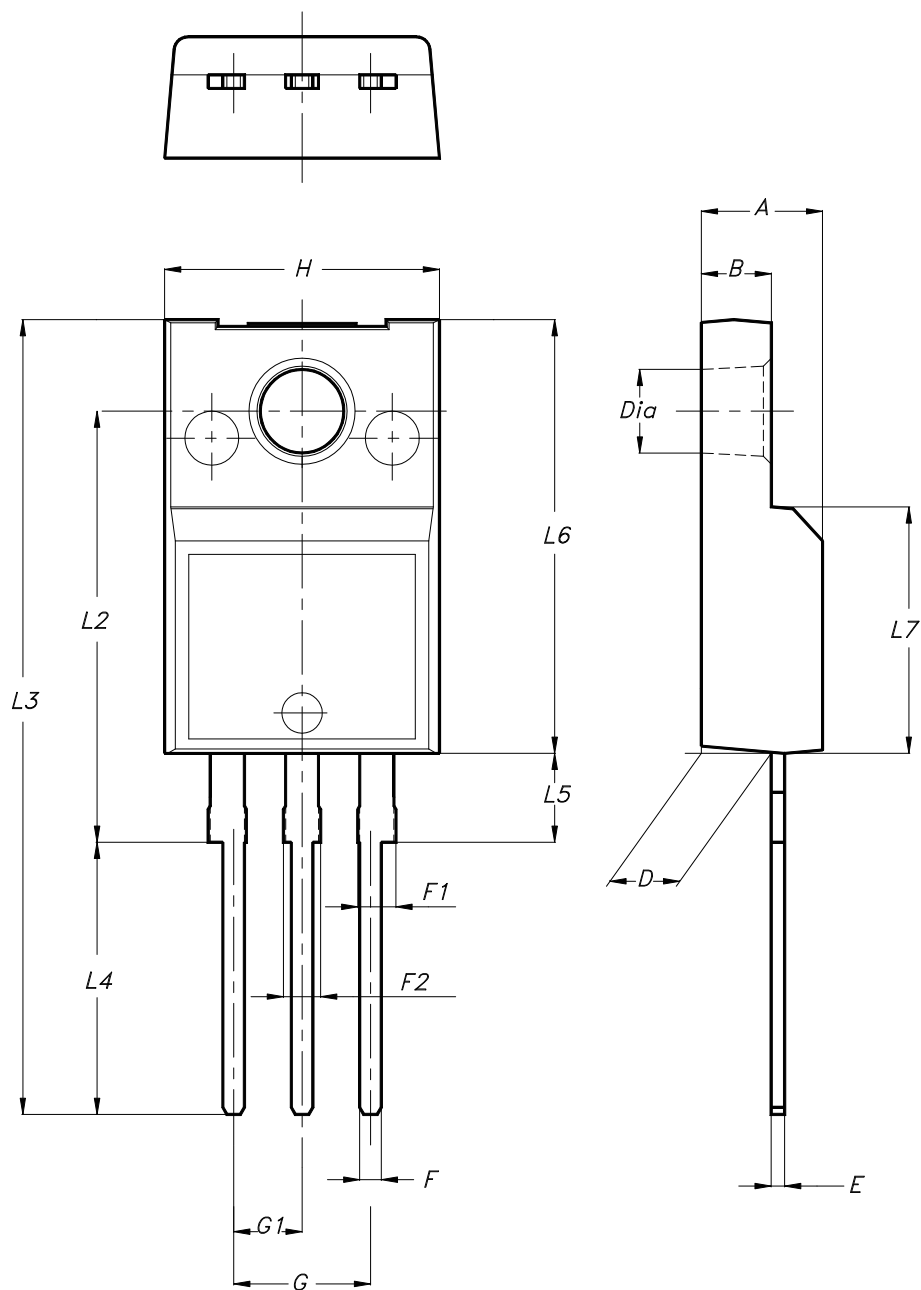
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.70	8.90	9.10
E2	7.30	7.50	7.70
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 29. D²PAK (TO-263) recommended footprint (dimensions are in mm)


0079457_Rev27_footprint

4.2 TO-220FP type B package information

Figure 30. TO-220FP type B package outline



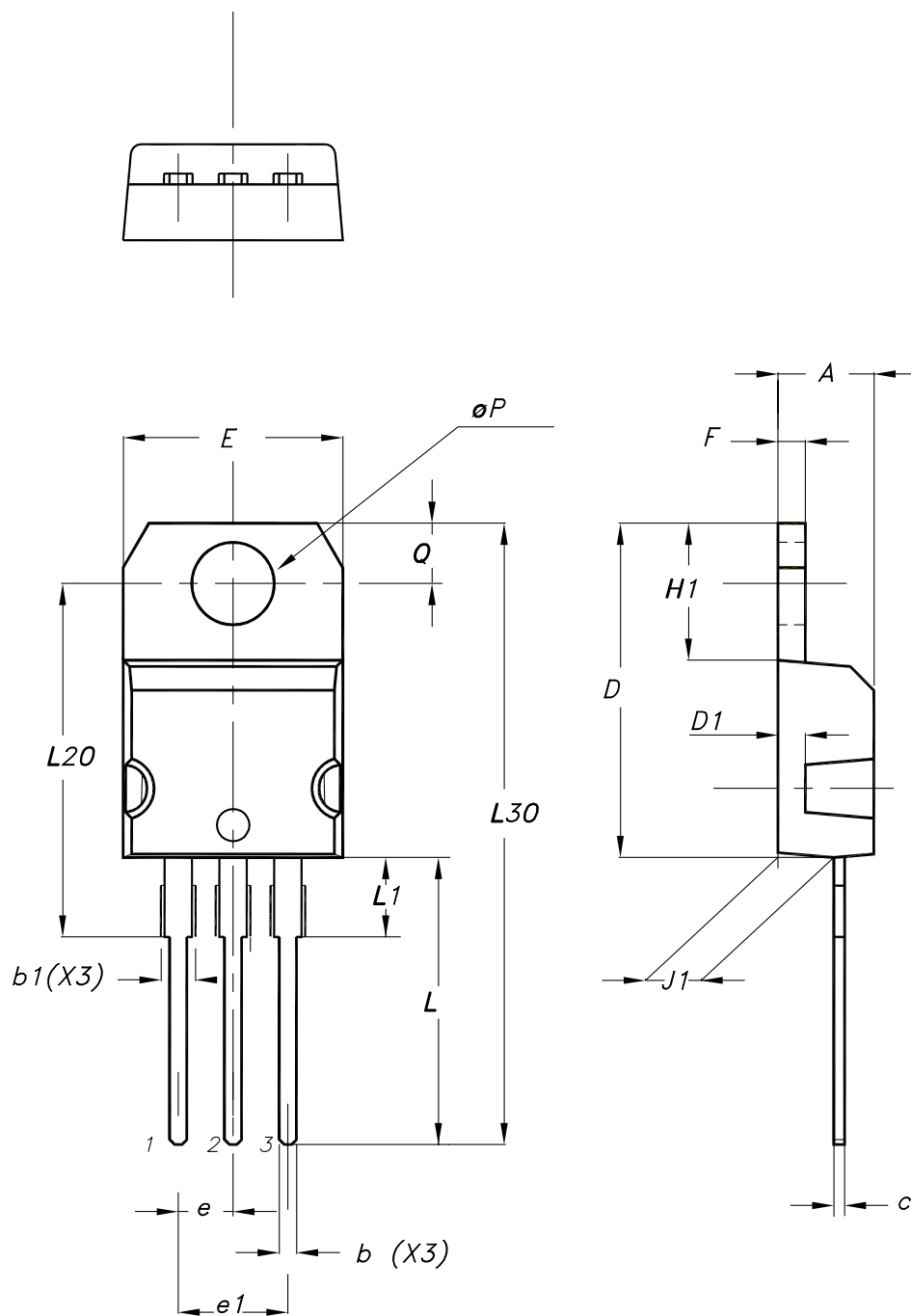
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Table 9. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.3 TO-220 type A package information

Figure 31. TO-220 type A package outline



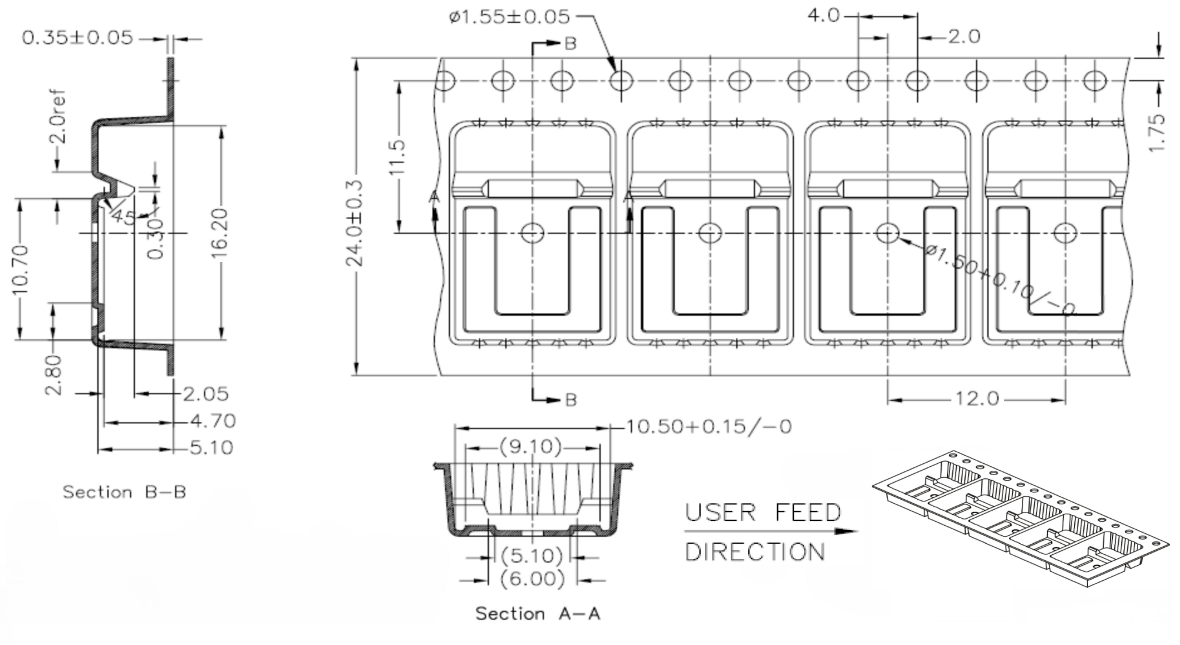
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Table 10. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

4.4 D²PAK packing information

Figure 32. D²PAK tape drawing (dimensions are in mm)



0079900_14



5 Ordering information

Table 11. Order codes

Order codes	Marking	Package	Packing
STGB20H60DF	GB20H60DF	D ² PAK	Tape and reel
STGF20H60DF	GF20H60DF	TO-220FP	Tube
STGP20H60DF	GP20H60DF	TO-220	

Revision history

Table 12. Document revision history

Date	Revision	Changes
03-Oct-2012	1	Initial release.
18-Mar-2013	2	Added new order code STGF20H60DF, mechanical data <i>Table 9</i> and <i>Figure 29</i> on page 14. Added <i>Chapter 2.1: Electrical characteristics (curves)</i> .
22-Mar-2013	3	Document status promoted from preliminary to production data.
03-Jun-2013	4	Updated PTOT in <i>Table 2: Absolute maximum ratings</i> , RthJC in <i>Table 3: Thermal data</i> and <i>Figure 10: Power dissipation vs. case temperature for D²PAK and TO-220</i> . Updated <i>Section 4: Package mechanical data</i> for TO-220.
23-May-2025	5	Updated <i>Table 1. Absolute maximum ratings</i> and <i>Section 4: Package information..</i>
12-Jun-2025	6	Updated <i>Table 1. Absolute maximum ratings</i> .



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4	Package information.....	11
4.1	D ² PAK (TO-263) type A2 package information	11
4.2	TO-220FP type B package information	14
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